



RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

RF Power transistors designed for applications operating at frequencies between 1.8 and 600 MHz. These devices are suitable for use in high VSWR industrial, broadcast and aerospace applications.

- Typical Performance: $V_{DD} = 50$ Volts, $I_{DQ} = 100$ mA

Signal Type	P_{out} (W)	f (MHz)	G_{ps} (dB)	η_D (%)	IRL (dB)
Pulsed (100 μ sec, 20% Duty Cycle)	300 Peak	230	26.5	74.0	-16
CW	300 Avg.	130	25.0	80.0	-15

- Capable of Handling a Load Mismatch of 65:1 VSWR, @ 50 Vdc, 230 MHz, at all Phase Angles
 - 300 Watts CW Output Power
 - 300 Watts Pulsed Peak Power, 20% Duty Cycle, 100 μ sec
- Capable of 300 Watts CW Operation

Features

- Device can be used Single-Ended or in a Push-Pull Configuration
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Qualified Up to a Maximum of 50 V_{DD} Operation
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- RoHS Compliant
- NI-780-4 in Tape and Reel. R3 Suffix = 250 Units, 56 mm Tape Width, 13 inch Reel.
- NI-780S-4 in Tape and Reel. R3 Suffix = 250 Units, 32 mm Tape Width, 13 inch Reel.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +125	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}$ C
Case Operating Temperature	T_C	150	$^{\circ}$ C
Operating Junction Temperature (1,2)	T_J	225	$^{\circ}$ C

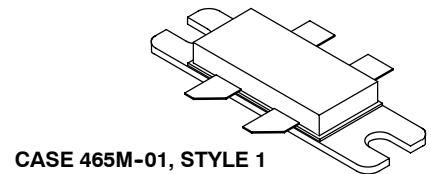
Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 75 $^{\circ}$ C, 300 W Pulsed, 100 μ sec Pulse Width, 20% Duty Cycle, 50 Vdc, $I_{DQ} = 100$ mA, 230 MHz	$Z_{\theta JC}$	0.05	$^{\circ}$ C/W
Case Temperature 87 $^{\circ}$ C, 300 W CW, 50 Vdc, $I_{DQ} = 1100$ mA, 230 MHz	$R_{\theta JC}$	0.19	

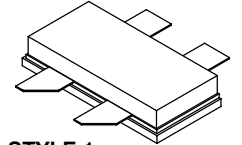
1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

MRFE6VP6300HR3
MRFE6VP6300HSR3

1.8-600 MHz, 300 W, 50 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 465M-01, STYLE 1
NI-780-4
MRFE6VP6300HR3



CASE 465H-02, STYLE 1
NI-780S-4
MRFE6VP6300HSR3

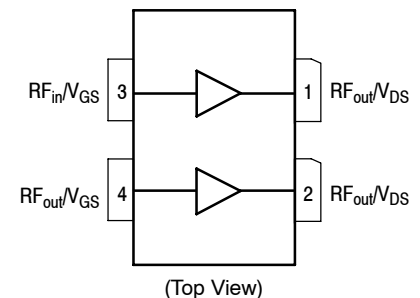


Figure 1. Pin Connections

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	B (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics ⁽¹⁾

Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 50\text{ mA}$)	$V_{(BR)DSS}$	125	—	—	Vdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	5	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 100\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 480\ \mu\text{Adc}$)	$V_{GS(th)}$	1.5	2.2	3.0	Vdc
Gate Quiescent Voltage ($V_{DD} = 50\text{ Vdc}$, $I_D = 100\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	1.7	2.5	3.2	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 1\text{ Adc}$)	$V_{DS(on)}$	—	0.25	—	Vdc

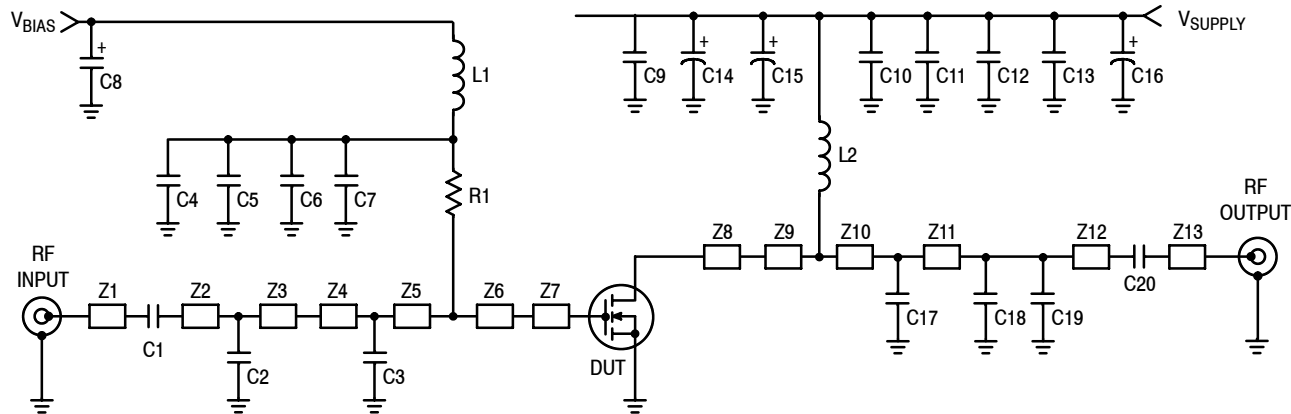
Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	0.8	—	pF
Output Capacitance ($V_{DS} = 50\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	76	—	pF
Input Capacitance ($V_{DS} = 50\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	188	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 50\text{ Vdc}$, $I_{DQ} = 100\text{ mA}$, $P_{out} = 300\text{ W Peak}$ (60 W Avg.), $f = 230\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle

Power Gain	G_{ps}	25.0	26.5	28.0	dB
Drain Efficiency	η_D	72.0	74.0	—	%
Input Return Loss	IRL	—	-16	-9	dB

1. Each side of device measured separately.



Z1	0.352" x 0.080" Microstrip	Z9	0.192" x 0.170" Microstrip
Z2*	1.780" x 0.080" Microstrip	Z10*	0.366" x 0.170" Microstrip
Z3*	0.576" x 0.080" Microstrip	Z11*	2.195" x 0.170" Microstrip
Z4	0.220" x 0.220" Microstrip	Z12*	0.614" x 0.170" Microstrip
Z5	0.322" x 0.220" Microstrip	Z13	0.243" x 0.080" Microstrip
Z6	0.168" x 0.220" Microstrip		
Z7, Z8	0.282" x 0.630" Microstrip		

* Line length includes microstrip bends

Figure 2. MRFE6VP6300HR3(HSR3) Test Circuit Schematic

Table 5. MRFE6VP6300HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C20	15 pF Chip Capacitors	ATC100B150JT500XT	ATC
C2	82 pF Chip Capacitor	ATC100B820JT500XT	ATC
C3, C17	91 pF Chip Capacitors	ATC100B910JT500XT	ATC
C4, C10	1000 pF Chip Capacitors	ATC100B102JT50XT	ATC
C5, C11	10K pF Chip Capacitors	ATC200B103KT50XT	ATC
C6	0.1 μ F, 50 V Chip Capacitor	CDR33BX104AKWS	AVX
C7	2.2 μ F, 100 V Chip Capacitor	HMK432B7225KM-T	Taiyo Yuden
C8	10 μ F, 35 V Tantalum Capacitor	T491D106K035AT	Kemet
C9	2.2 μ F, 100 V Chip Capacitor	G2225X7R225KT3AB	ATC
C12	0.1 μ F, 100 V Chip Capacitor	C1812F104K1RAC	Kemet
C13	0.01 μ F, 100 V Chip Capacitor	C1825C103K1GAC	Kemet
C14, C15, C16	220 μ F, 100 V Electrolytic Capacitors	MCGPR100V227M16X26-RH	Multicomp
C18, C19	18 pF Chip Capacitors	ATC100B180JT500XT	ATC
L1	120 nH Inductor	1812SMS-R12JLC	Coilcraft
L2	17.5 nH Inductor	GA3095-ALC	Coilcraft
R1	1000 Ω , 1/2 W Chip Resistor	CRCW20101K00FKEF	Vishay
PCB	0.030", $\epsilon_r = 2.55$	AD255A	Arlon

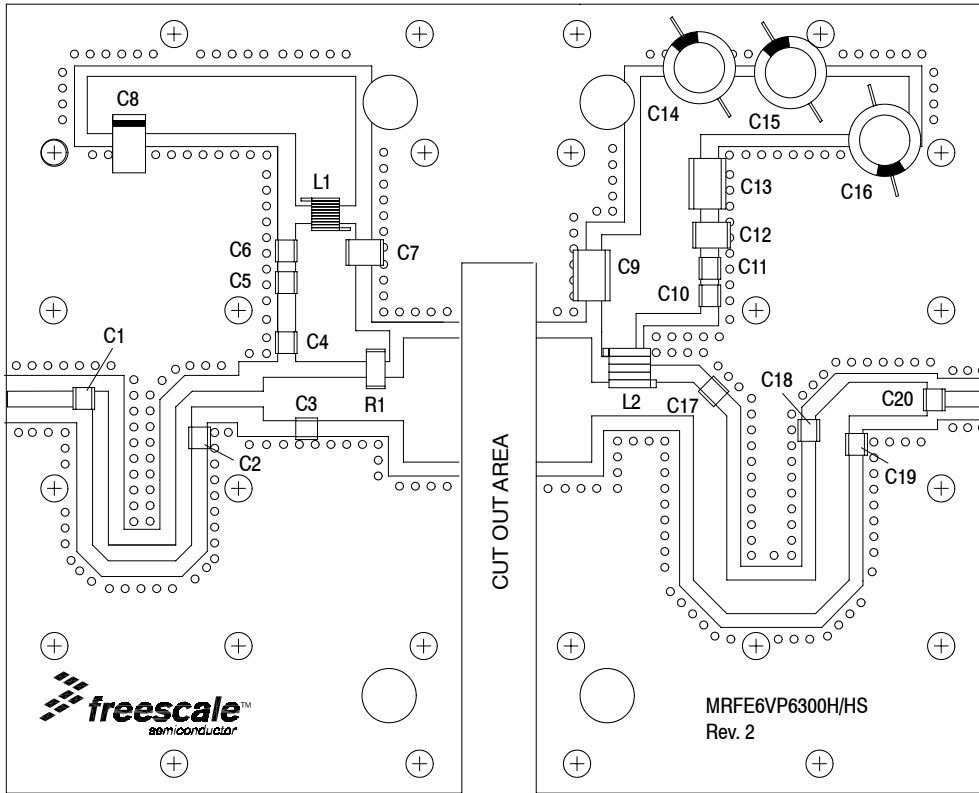
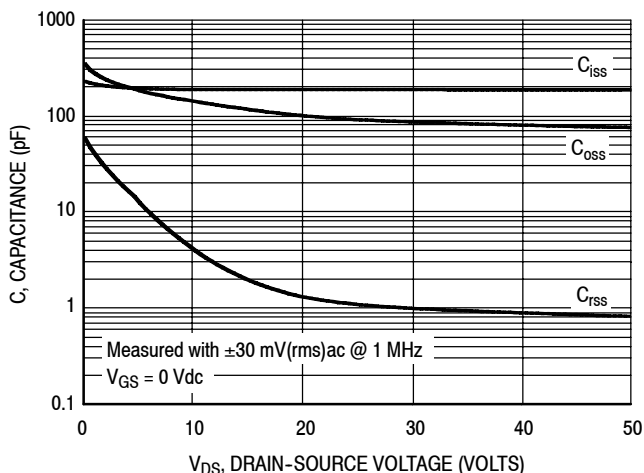


Figure 3. MRFE6VP6300HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS — PULSED



Note: Each side of device measured separately.

Figure 4. Capacitance versus Drain-Source Voltage

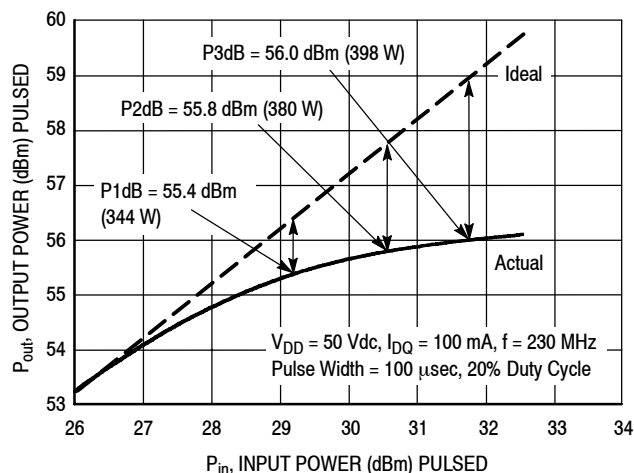


Figure 5. Pulsed Output Power versus Input Power

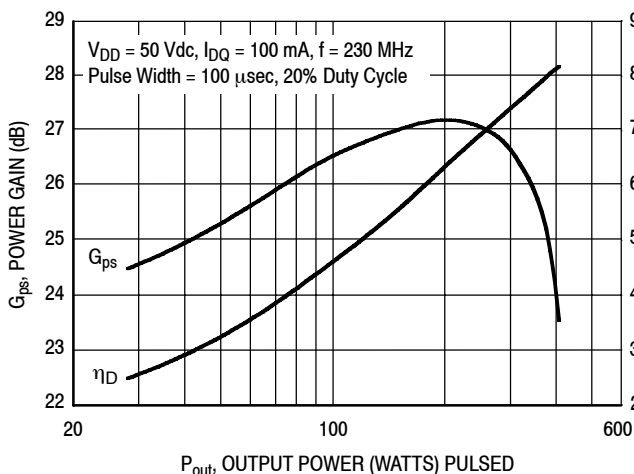


Figure 6. Pulsed Power Gain and Drain Efficiency versus Output Power

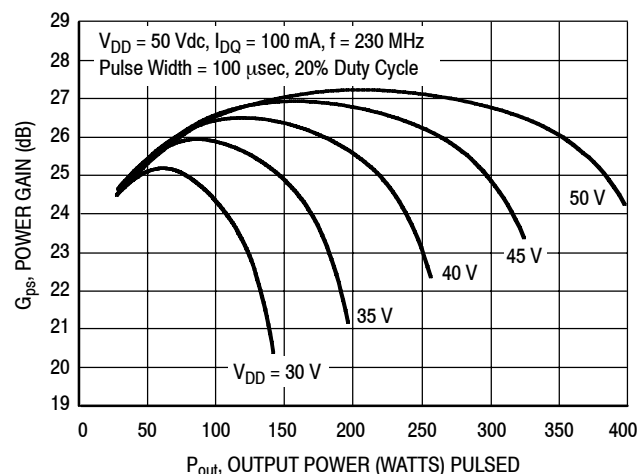


Figure 7. Pulsed Power Gain versus Output Power

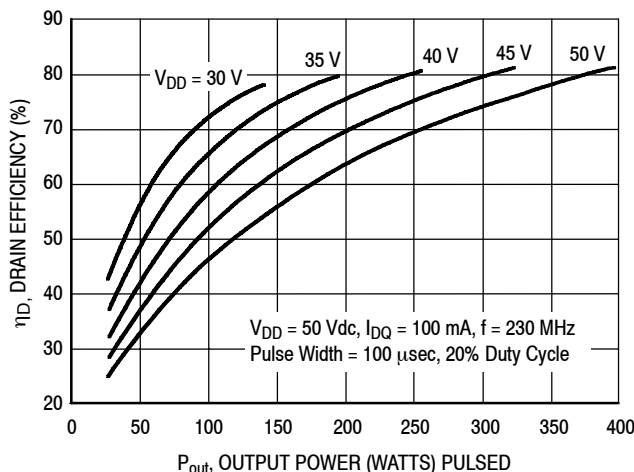


Figure 8. Pulsed Drain Efficiency versus Output Power

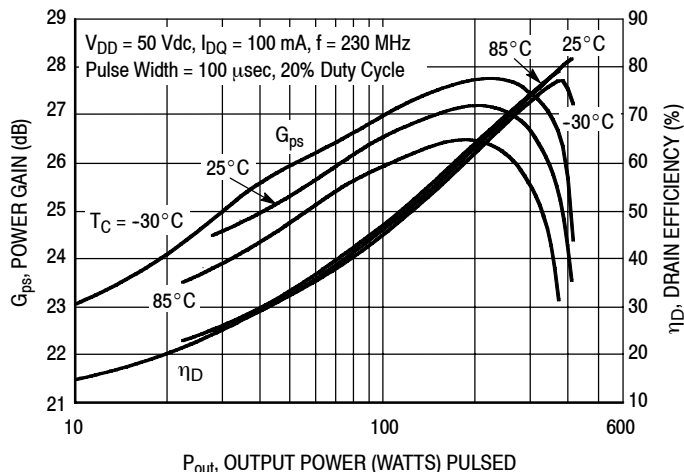


Figure 9. Pulsed Power Gain and Drain Efficiency versus Output Power

MRFE6VP6300HR3 MRFE6VP6300HSR3

TYPICAL CHARACTERISTICS — TWO-TONE

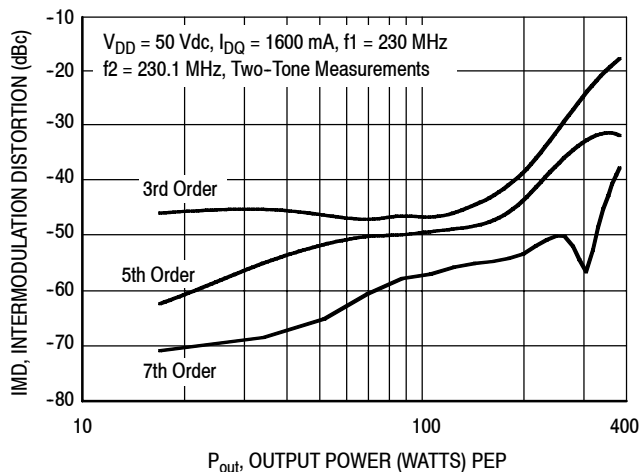


Figure 10. Intermodulation Distortion Products versus Output Power

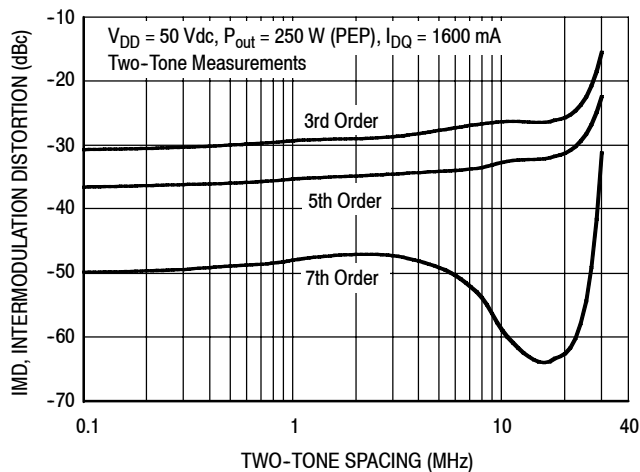


Figure 11. Intermodulation Distortion Products versus Two-Tone Spacing

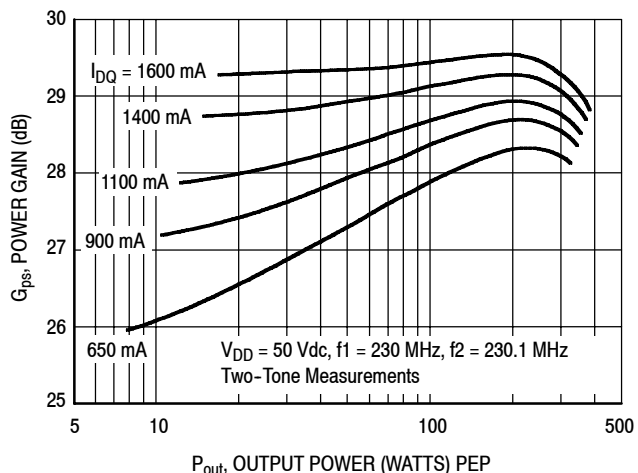


Figure 12. Two-Tone Power Gain versus Output Power

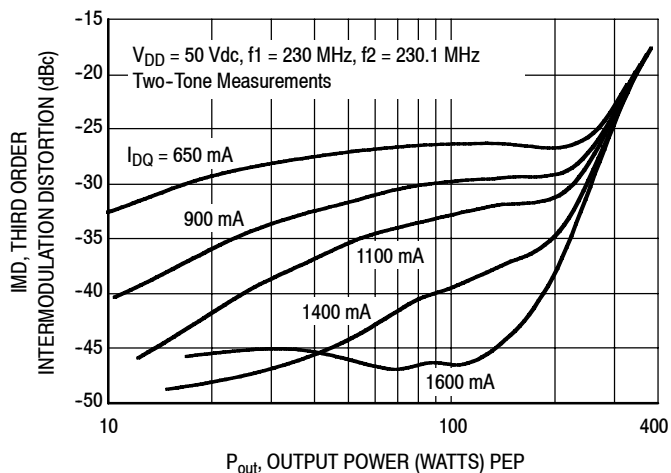
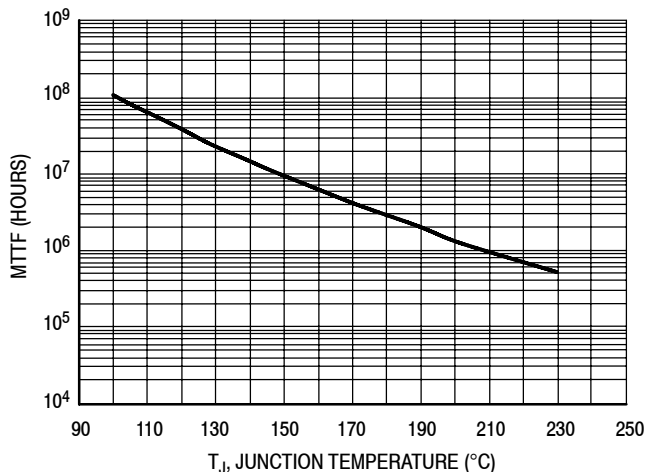


Figure 13. Third Order Intermodulation Distortion versus Output Power

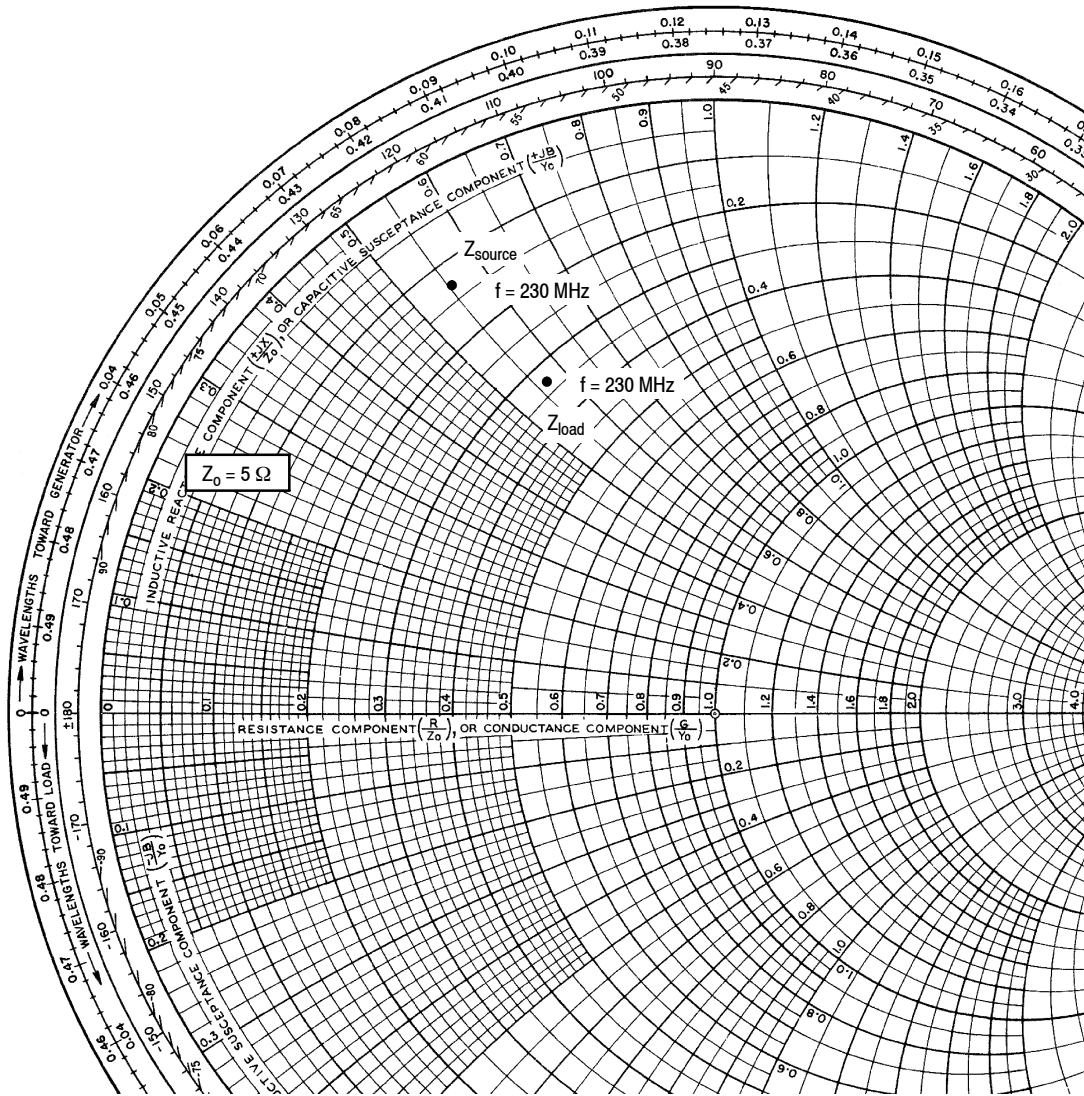
TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 50$ Vdc, $P_{out} = 300$ W Avg., and $\eta_D = 80\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 14. MTTF versus Junction Temperature — CW



$V_{DD} = 50 \text{ Vdc}$, $I_{DQ} = 100 \text{ mA}$, $P_{out} = 300 \text{ W Peak}$

f MHz	Z_{source} Ω	Z_{load} Ω
230	$0.65 + j2.79$	$1.64 + j2.85$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

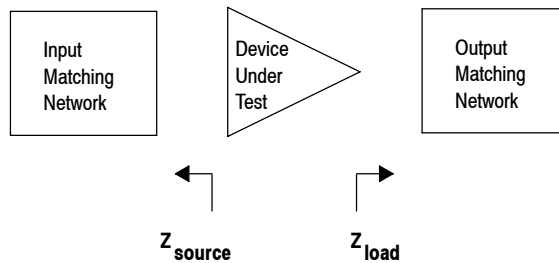
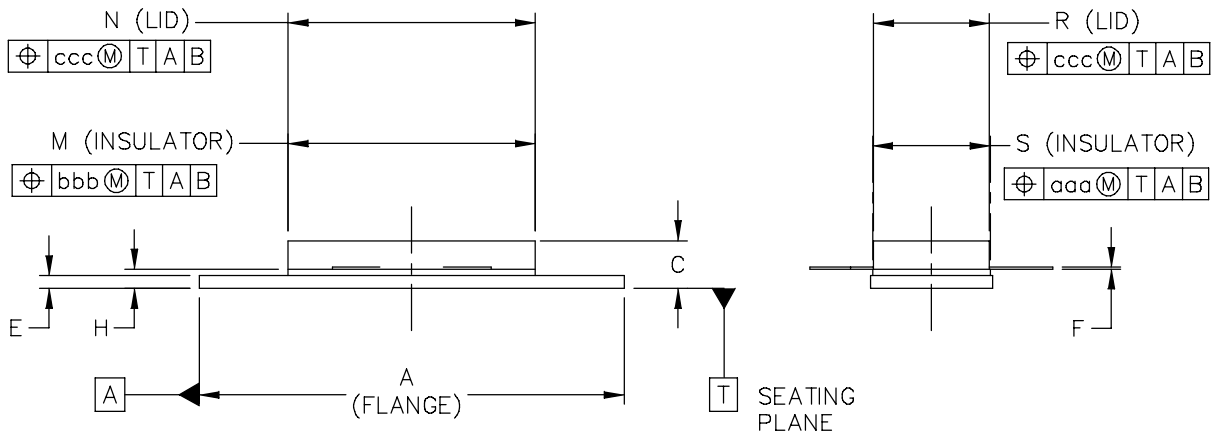
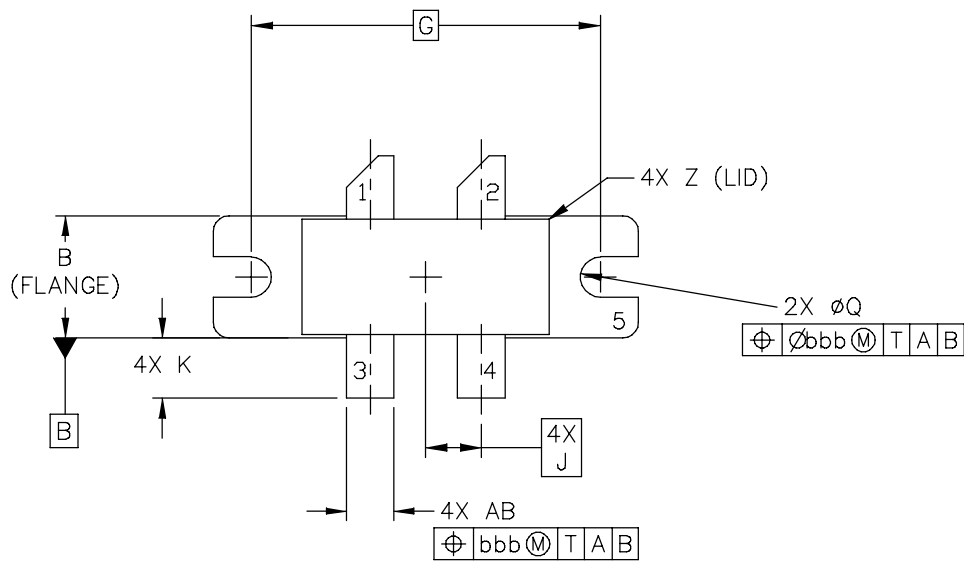


Figure 15. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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	CASE NUMBER: 465M-01	27 MAR 2007	
	STANDARD: NON-JEDEC		

MRFE6VP6300HR3 MRFE6VP6300HSR3

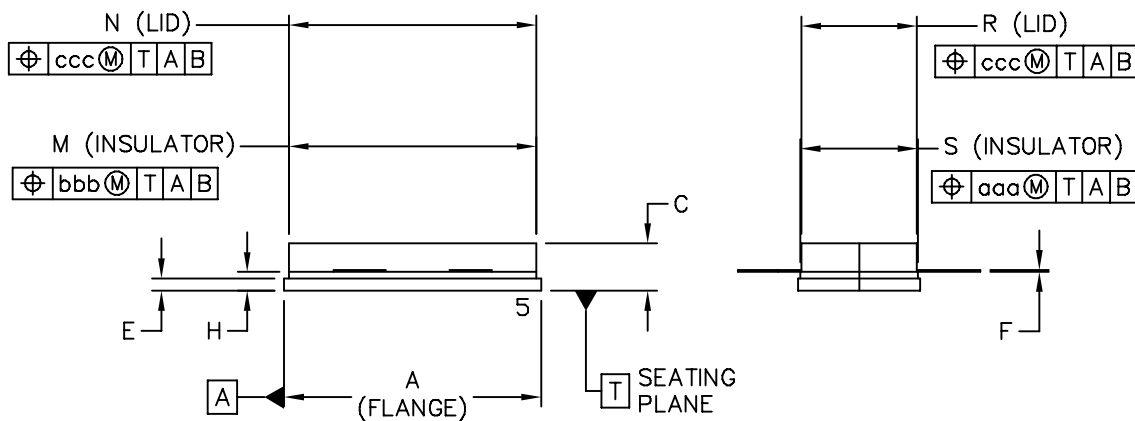
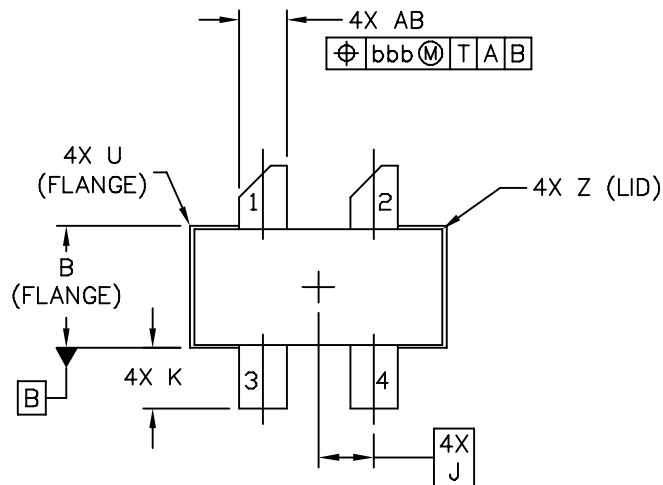
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN
1. DRAIN
 2. DRAIN
 3. GATE
 4. GATE
 5. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16	R	.365	.375	9.27	9.53
B	.380	.390	9.65	9.91	S	.365	.375	9.27	9.52
C	.125	.170	3.18	4.32	U		.040		1.02
E	.035	.045	0.89	1.14	Z		.030		0.76
F	.003	.006	0.08	0.15	AB	.145	.155	3.68	3.94
G	1.100 BSC		27.94 BSC						
H	.057	.067	1.45	1.7	aaa		.005		0.127
J	.175 BSC		4.44 BSC		bbb		.010		0.254
K	.170	.210	4.32	5.33	ccc		.015		0.381
M	.774	.786	19.61	20.02					
N	.772	.788	19.61	20.02					
Q	ø.118	ø.138	ø3	ø3.51					
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4. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. GATE
 5. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.805	.815	20.45	20.7	U		.040		1.02
B	.380	.390	9.65	9.91	Z		.030		0.76
C	.125	.170	3.18	4.32	AB	.145	.155	3.68	- 3.94
E	.035	.045	0.89	1.14					
F	.003	.006	0.08	0.15	aaa		.005		0.127
H	.057	.067	1.45	1.7	bbb		.010		0.254
J	.175 BSC		4.44 BSC		ccc		.015		0.381
K	.170	.210	4.32	5.33					
M	.774	.786	19.61	20.02					
N	.772	.788	19.61	20.02					
R	.365	.375	9.27	9.53					
S	.365	.375	9.27	9.52					
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					CASE NUMBER: 465H-02			27 MAR 2007	
					STANDARD: NON-JEDEC				

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model
- .s2p File

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Oct. 2010	• Initial Release of Data Sheet

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